

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	139	power adj3 semiconductor adj3 switching adj3 device	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 14:57
2	BRS	L2	1	1 and (backside adj3 emitter)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 14:57
3	BRS	L3	1	1 and (residual adj3 diffused)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 14:58
4	BRS	L4	5	1 and (ion adj3 implantation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 14:58

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1	nonuniformly adj3 doped adj3 n adj3 type adj3 substrate	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 16:06
2	BRS	L2	13723	IGBT or MCT or GTO	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 16:06
3	BRS	L3	201	2 and (diffused adj3 layer)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 16:25
4	BRS	L5	2	4 and (residual adj3 diffused)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 16:26
5	BRS	L4	109	3 and (thin or thinning)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 17:40

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	1	(low adj3 power adj3 loss) adj10 IGBT	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 17:40
7	BRS	L7	1	(low adj3 power adj3 loss) adj10 (IGBT or (insulated adj gate adj bipolar adj transistor))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 17:42
8	BRS	L8	5	(low adj3 power adj3 loss) same (IGBT or (insulated adj gate adj bipolar adj transistor))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 18:01
9	IS&R	L9	99	(438/212).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 18:13
10	IS&R	L10	376	(257/327).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/09/19 18:13